

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
60V	3.1mΩ @ V _{GS} = 10V	90A
	4.5mΩ @ V _{GS} = 4.5V	85A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Primary Switch in Isolated DC-DC
- Synchronous Rectifier
- Loadswitch

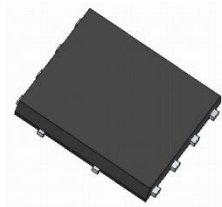
Features

- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – Minimizes Power Losses
- Low Q_G – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

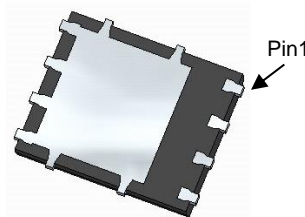
Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.097 grams (Approximate)

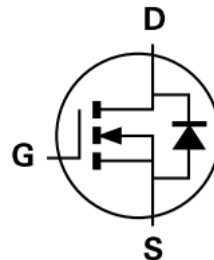
PowerDI5060-8



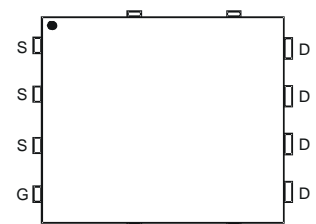
Top View



Bottom View



Internal Schematic



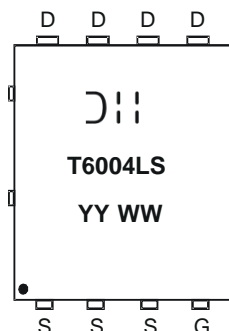
Top View
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6004LPS-13	PowerDI5060-8	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



☐:: = Manufacturer's Marking
 T6004LS = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 15 = 2015)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 5)	T _A = +25°C	I _D	22	A
	T _A = +70°C		16	
Continuous Drain Current (Note 6)	T _C = +25°C	I _D	90	A
	T _C = +70°C (Note 8)		90	
Maximum Continuous Body Diode Forward Current (Note 6)		I _S	90	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I _{DM}	100	A
Avalanche Current, L = 0.2mH		I _{AS}	40	A
Avalanche Energy, L = 0.2mH		E _{AS}	160	mJ

Thermal Characteristic

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{θJA}	47	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	105	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	1	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	2.5	3.1	mΩ	V _{GS} = 10V, I _D = 25A
		—	3.3	4.5	mΩ	V _{GS} = 4.5V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	—	1.3	V	V _{GS} = 0V, I _S = 25A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	4,515	—	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	—	1,477	—		
Reverse Transfer Capacitance	C _{RSS}	—	135.3	—		
Gate Resistance	R _G	—	0.64	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _G	—	96.3	—	nC	V _{DD} = 30V, I _D = 25A
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	47.4	—		
Gate-Source Charge	Q _{GS}	—	14.1	—		
Gate-Drain Charge	Q _{GD}	—	21.4	—		
Turn-On Delay Time	t _{D(ON)}	—	9.9	—	ns	V _{DD} = 30V, V _{GS} = 10V, I _D = 25A, R _G = 3.5Ω
Turn-On Rise Time	t _R	—	17.7	—		
Turn-Off Delay Time	t _{D(OFF)}	—	53.5	—		
Turn-Off Fall Time	t _F	—	32.9	—		
Body Diode Reverse Recovery Time	t _{RR}	—	49.7	—	ns	I _F = 25A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	78.9	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

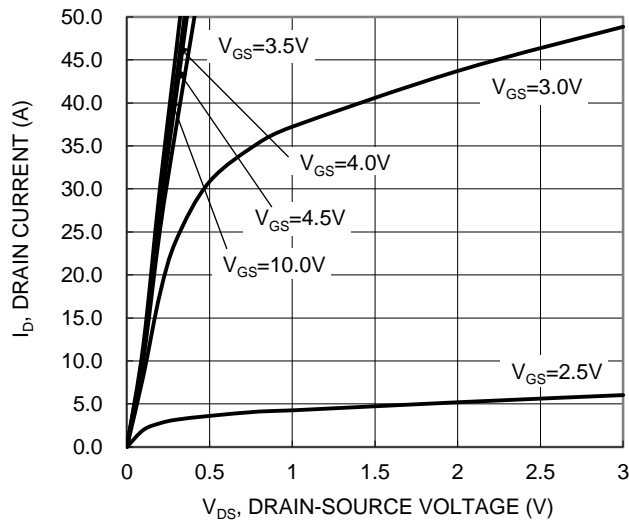


Figure 1. Typical Output Characteristic

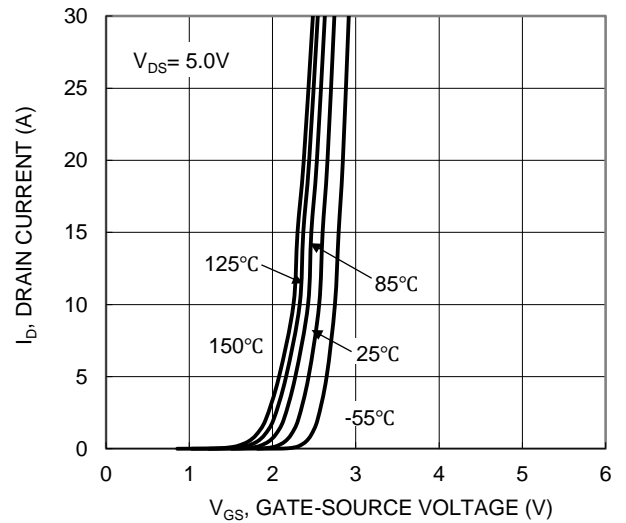


Figure 2. Typical Transfer Characteristic

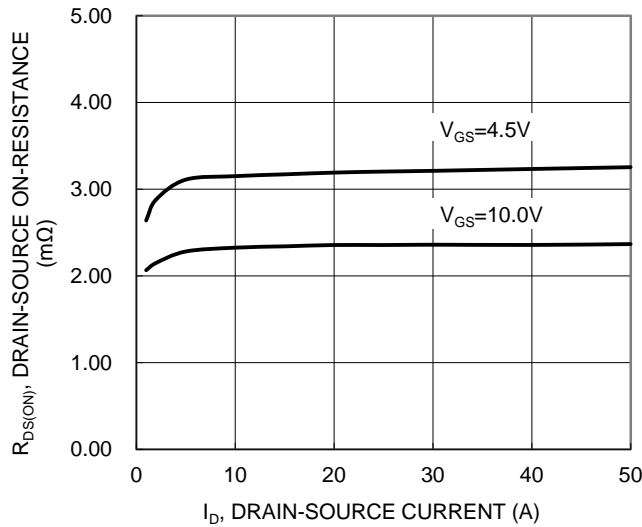


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

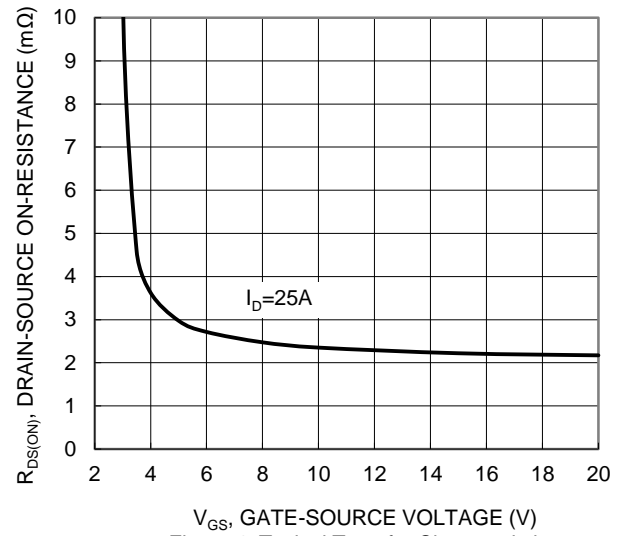


Figure 4. Typical Transfer Characteristic

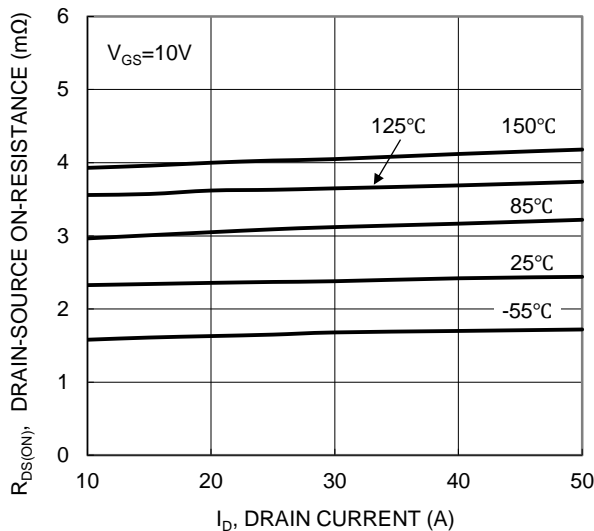


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

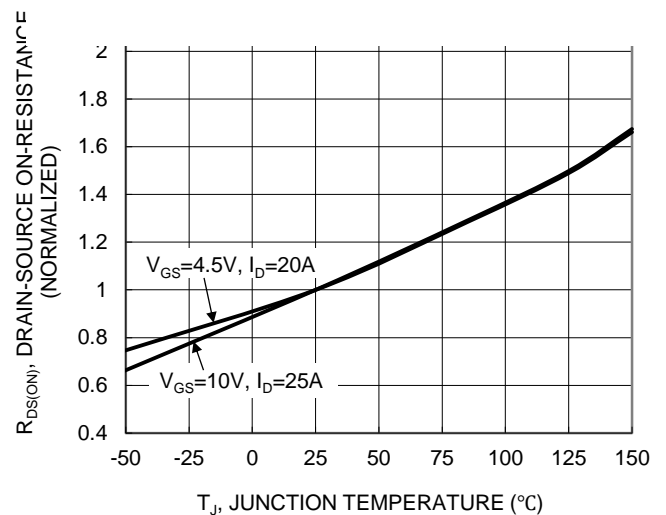
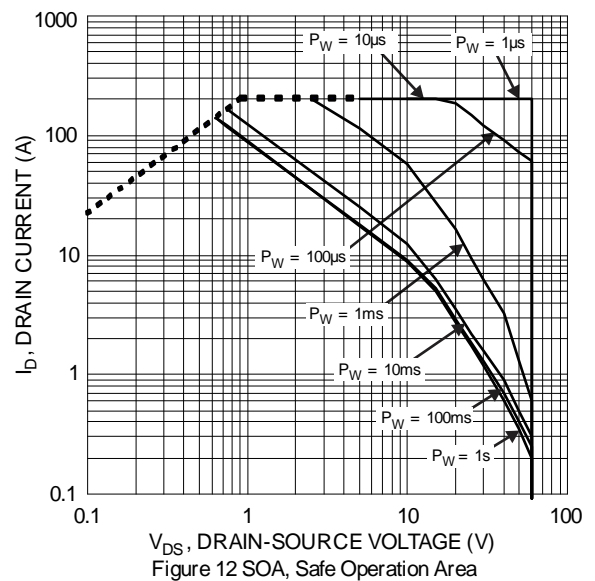
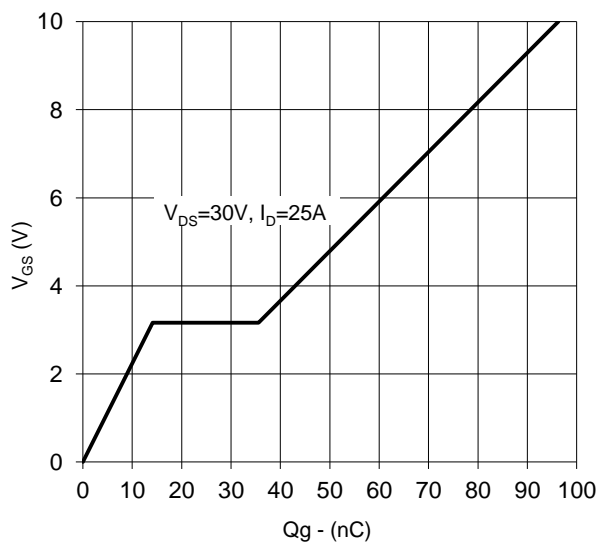
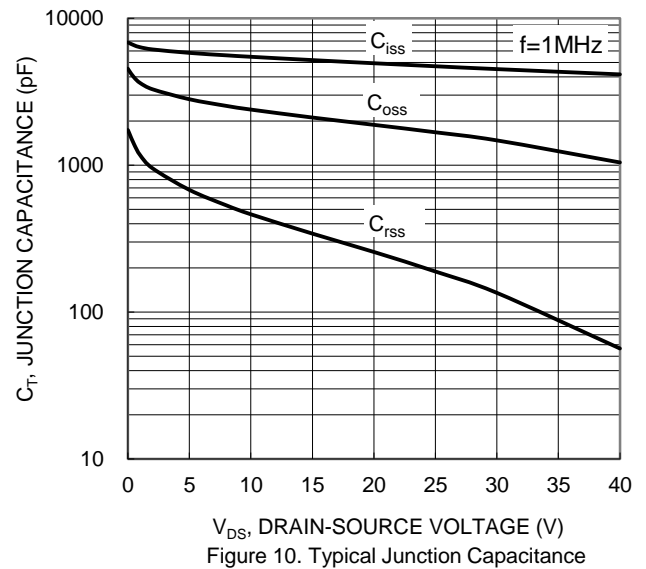
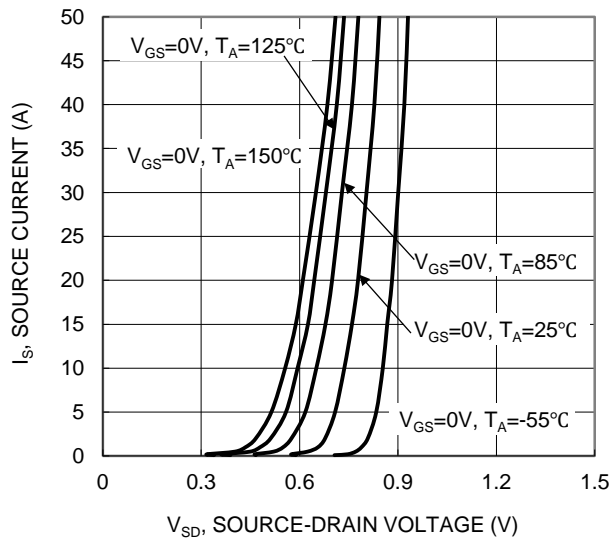
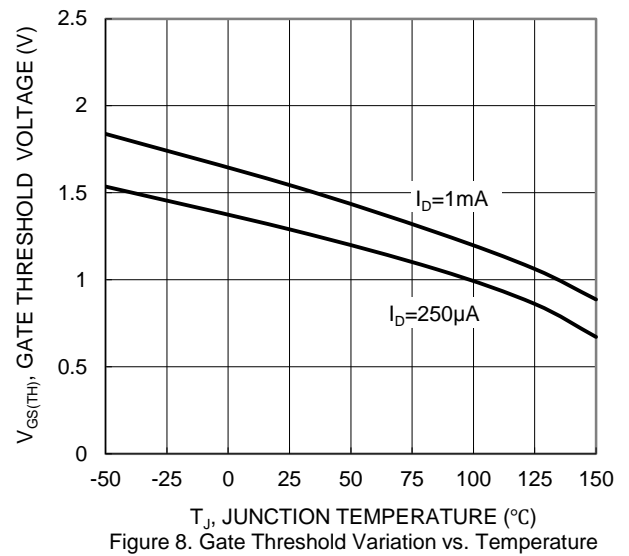
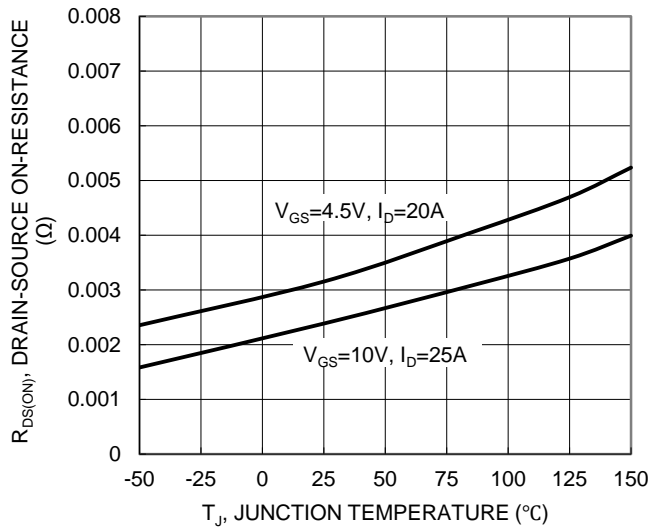


Figure 6. On-Resistance Variation with Temperature



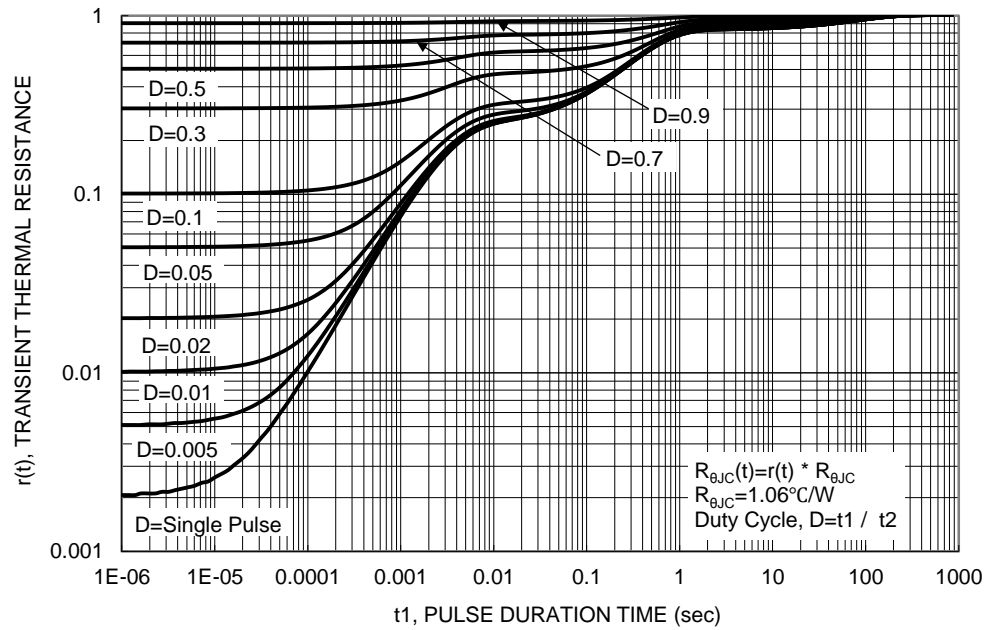
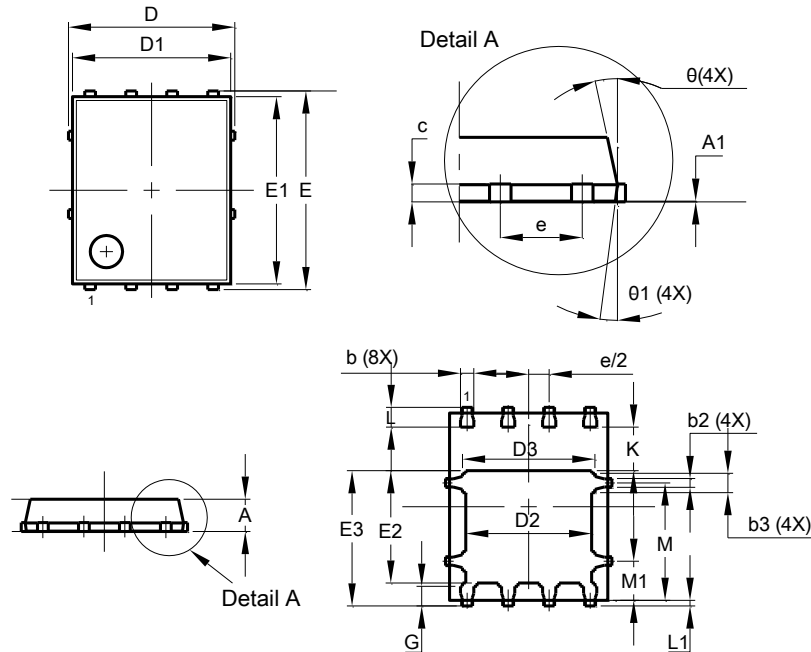


Figure 12. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

PowerDI5060-8

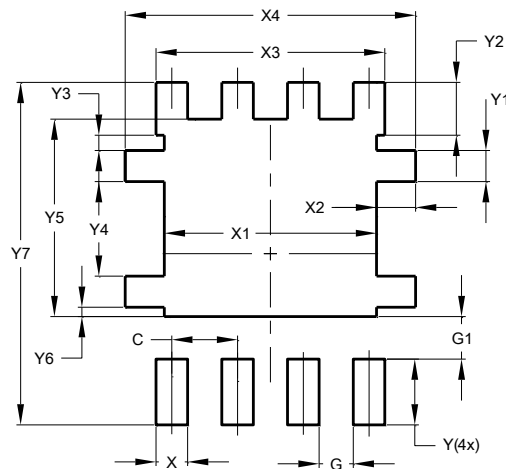


PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
$\theta1$	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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